



## UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE  
 United States Patent and Trademark Office  
 Address: COMMISSIONER FOR PATENTS  
 P.O. Box 1450  
 Alexandria, Virginia 22313-1450  
[www.uspto.gov](http://www.uspto.gov)



Bib Data Sheet

CONFIRMATION NO. 8834

SERIAL NUMBER 10/538,878	FILING OR 371(c) DATE 06/14/2005 RULE	CLASS 117	GROUP ART UNIT 1722	ATTORNEY DOCKET NO. 124231
-----------------------------	--	--------------	------------------------	----------------------------------

## APPLICANTS

Masahiro Sakurada, Fukushima, JAPAN;  
 Izumi Fusegawa, Fukushima, JAPAN;

## \*\* CONTINUING DATA \*\*\*\*\*

This application is a 371 of PCT/JP03/16794 12/25/2003

## \*\* FOREIGN APPLICATIONS \*\*\*\*\*

JAPAN 2003-10436 01/17/2003

Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no	STATE OR COUNTRY JAPAN	SHEETS DRAWING 4	TOTAL CLAIMS 28	INDEPENDENT CLAIMS 2
35 USC 119 (a-d) conditions <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after time Initials				
Verified and Acknowledged <i>A. Bush</i> Examiner's Signature				

## ADDRESS

25944

## TITLE

Process for producing p doped silicon single crystal and p doped n type silicon single crystal wafer

FILING FEE RECEIVED 1300	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:	<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees ( Filing ) <input type="checkbox"/> 1.17 Fees ( Processing Ext. of time ) <input type="checkbox"/> 1.18 Fees ( Issue ) <input type="checkbox"/> Other _____ <input type="checkbox"/> Credit
-----------------------------	---	---